

# **DSF20545SF**

# **Fast Recovery Diode**

 $V_{RRM}$ 

 $\mathbf{I}_{\mathrm{F(AV)}}$ 

Replaces January 2000 version, DS4152-4.0

DS4152-5.0 June 2004

4500V

1256A

16000A

1250μC

**7.0**μs

**KEY PARAMETERS** 

# **APPLICATIONS**

- Induction Heating
- A.C. Motor Drives
- Inverters And Choppers
- Welding
- High Frequency Rectification
- **■** UPS

#### **FEATURES**

- Double Side Cooling
- High Surge Capability
- Low Recovery Charge

# **VOLTAGE RATINGS**

Type Number	Repetitive Peak Reverse Voltage V <sub>RRM</sub> V	Conditions
DSF20545SF45	4500	$V_{RSM} = V_{RRM} + 100V$
DSF20545SF44	4400	TIOW THAN
DSF20545SF43	4300	
DSF20545SF42	4200	
DSF20545SF41	4100	
DSF20545SF40	4000	

Lower voltage grades available.

# Outline type code: CB450. See Package Details for further information.

Fig. 1 Package outline

#### **ORDERING INFORMATION**

When ordering, select the required part number shown in the Voltage Ratings selection table, e.g.:

#### DSF20545SF43

Note: Please use the complete part number when ordering and quote this number in any future correspondance relating to your order.



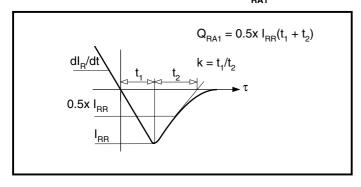
# **CURRENT RATINGS**

Symbol	Parameter	Conditions		Units			
Double Sid	Double Side Cooled						
I <sub>F(AV)</sub>	Mean forward current	Half wave resistive load, T <sub>case</sub> = 65°C	1256	Α			
I <sub>F(RMS)</sub>	RMS value	T <sub>case</sub> = 65°C	1971	Α			
I <sub>F</sub>	Continuous (direct) forward current	T <sub>case</sub> = 65°C	1765	Α			
Single Side Cooled (Anode side)							
I <sub>F(AV)</sub>	Mean forward current	Half wave resistive load, T <sub>case</sub> = 65°C	995	Α			
I <sub>F(RMS)</sub>	RMS value	T <sub>case</sub> = 65°C	1552	Α			
I <sub>F</sub>	Continuous (direct) forward current	T <sub>case</sub> = 65°C	1335	Α			

# **SURGE RATINGS**

Symbol	Parameter	Conditions	Max.	Units
I <sub>FSM</sub>	Surge (non-repetitive) forward current	10ms half sine; with 09/ V T = 150°C	16	kA
l <sup>2</sup> t	I <sup>2</sup> t for fusing	10ms half sine; with 0% $V_{RRM}$ , $T_j = 150$ °C	1280 x 10 <sup>3</sup>	A²s
I <sub>FSM</sub>	Surge (non-repetitive) forward current	10ms half sine; with 50% V <sub>RBM</sub> T <sub>i</sub> = 150°C	12.8	kA
l <sup>2</sup> t	I <sup>2</sup> t for fusing		819.2 X 10 <sup>3</sup>	A <sup>2</sup> s
I <sub>FSM</sub>	Surge (non-repetitive) forward current	10ms half sine; with 100% V <sub>RRM</sub> T <sub>i</sub> = 150°C	-	kA
l²t	I <sup>2</sup> t for fusing	101115 Hall Sille, With 100 /6 V <sub>RRM</sub> , 1 <sub>j</sub> = 130 C	-	A²s

# DEFINITION OF K FACTOR AND $\boldsymbol{Q}_{\text{RA1}}$





# THERMAL AND MECHANICAL DATA

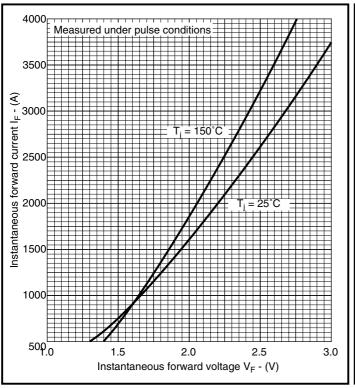
Symbol	Parameter	Conditions		Min.	Max.	Units
$R_{th(j-c)}$	Thermal resistance - junction to case	Double side cooled	dc	-	0.022	°C/W
		Single side cooled	Anode dc	-	0.032	°C/W
			Cathode dc	-	0.032	°C/W
R <sub>th(c-h)</sub>	Thermal resistance - case to heatsink	Clamping force 15kN with mounting compound	Double side	-	0.004	°C/W
			Single side	-	0.008	°C/W
T <sub>vj</sub>	Virtual junction temperature	On-state (conducting)		-	150	°C
T <sub>stg</sub>	Storage temperature range			-55	150	°C
-	Clamping force			17.5	21.5	kN

# **CHARACTERISTICS**

Symbol	Parameter	Conditions	Тур.	Max.	Units
V <sub>FM</sub>	Forward voltage	At 1800A peak, T <sub>case</sub> = 25°C	-	2.1	\ \
I <sub>RRM</sub>	Peak reverse current	At V <sub>RRM</sub> , T <sub>case</sub> = 150°C	-	50	mA
t <sub>rr</sub>	Reverse recovery time		-	7.0	μs
Q <sub>RA1</sub>	Recovered charge (50% chord)	$I_F = 1000A$ , $di_{RR}/dt = 100A/\mu s$	-	1250	μС
I <sub>RM</sub>	Reverse recovery current	$T_{case} = 150^{\circ}C, V_{R} = 100V$	-	400	Α
К	Soft factor		1.8	-	-
V <sub>TO</sub>	Threshold voltage	At T <sub>vj</sub> = 150°C	-	1.36	٧
r <sub>T</sub>	Slope resistance	At T <sub>vj</sub> = 150°C	-	0.47	mΩ
V <sub>FRM</sub>	Forward recovery voltage	di/dt = 1000A/μs, T <sub>j</sub> = 125°C	-	160	V



# **CURVES**



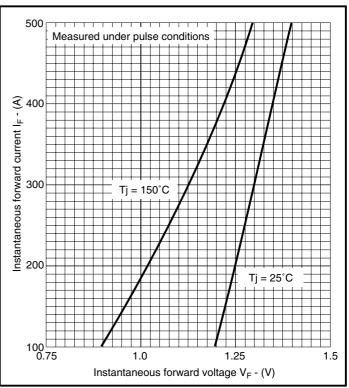


Fig.2 Maximum (limit) forward characteristics

Fig.3 Maximum (limit) forward characteristics

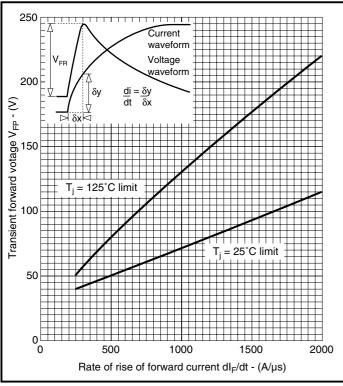


Fig.4 Transient forward voltage vs rate of rise of forward current

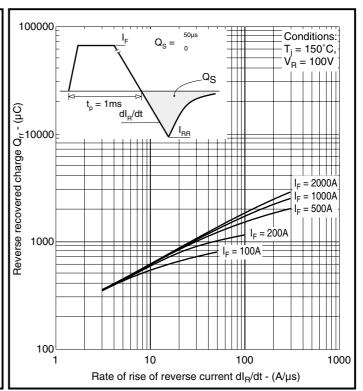
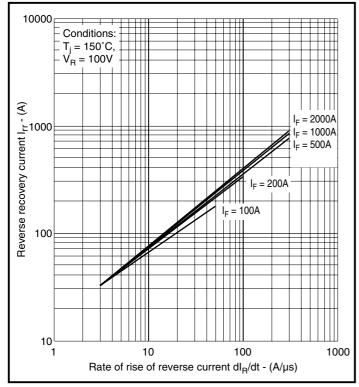


Fig.5 Recovered charge





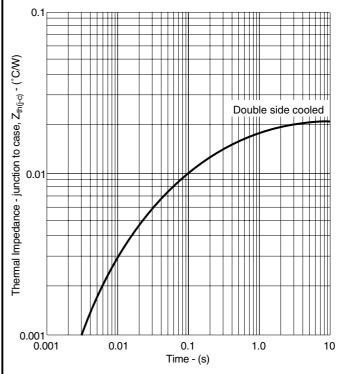


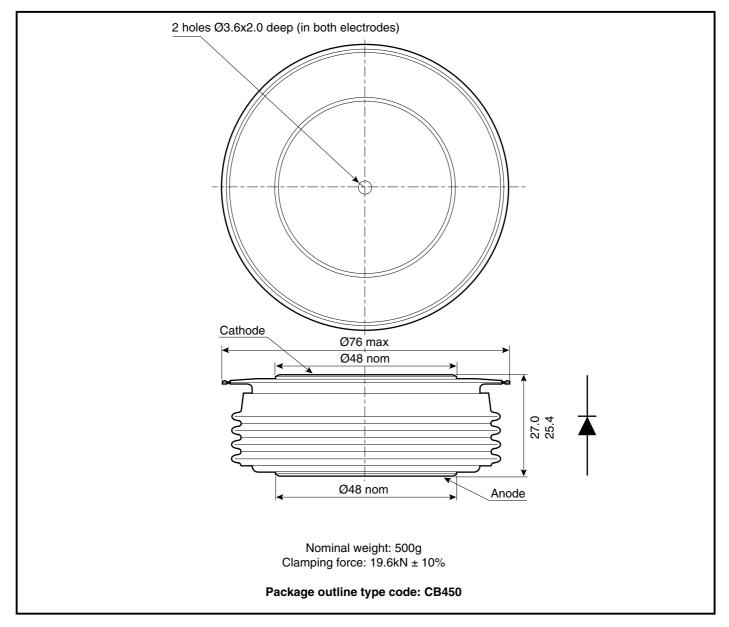
Fig.6 Typical reverse recovery current vs rate of rise of forward current

Fig.7 Maximum (limit) transient thermal impedance - junction to case - (°C/W)



# **PACKAGE DETAILS**

For further package information, please contact Customer Services. All dimensions in mm, unless stated otherwise. DO NOT SCALE.



#### POWER ASSEMBLY CAPABILITY

The Power Assembly group was set up to provide a support service for those customers requiring more than the basic semiconductor, and has developed a flexible range of heatsink and clamping systems in line with advances in device voltages and current capability of our semiconductors.

We offer an extensive range of air and liquid cooled assemblies covering the full range of circuit designs in general use today. The Assembly group offers high quality engineering support dedicated to designing new units to satisfy the growing needs of our customers.

Using the latest CAD methods our team of design and applications engineers aim to provide the Power Assembly Complete Solution (PACs).

#### **HEATSINKS**

The Power Assembly group has its own proprietary range of extruded aluminium heatsinks which have been designed to optimise the performance of Dynex semiconductors. Data with respect to air natural, forced air and liquid cooling (with flow rates) is available on request.

For further information on device clamps, heatsinks and assemblies, please contact your nearest sales representative or Customer Services.

Stresses above those listed in this data sheet may cause permanent damage to the device. In extreme conditions, as with all semiconductors, this may include potentially hazardous rupture of the package. Appropriate safety precautions should always be followed.



http://www.dynexsemi.com

e-mail: power\_solutions@dynexsemi.com

HEADQUARTERS OPERATIONS
DYNEX SEMICONDUCTOR LTD
Doddington Road, Lincoln.
Lincolnshire. LN6 3LF. United Kingdom.
Tel: +44-(0)1522-500500
Fax: +44-(0)1522-500550

CUSTOMER SERVICE Tel: +44 (0)1522 502753 / 502901. Fax: +44 (0)1522 500020

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